

# Shinobu Ohya

## List of Publications by Year in descending order

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77  
papers

1,531  
citations

377584

21  
h-index

371746

37  
g-index

82  
all docs

82  
docs citations

82  
times ranked

1544  
citing authors

#	ARTICLE	IF	CITATIONS
1	Theoretical analysis of the inverse Edelstein effect at the LaAlO <sub>3</sub> /SrTiO <sub>3</sub> interface with an effective tight-binding model: important role of the second d <sub>xy</sub> subband. Applied Physics Express, 2022, 15, 013005.	1.1	3
2	Bias-dependent two-phase anisotropy in magnetoresistance of a GaMnAs-based magnetic tunnel junction. Applied Physics Express, 2022, 15, 033001.	1.1	1
3	Thickness-dependent quantum transport of Weyl fermions in ultra-high-quality SrRuO <sub>3</sub> films. Applied Physics Letters, 2021, 118, 092408.	1.5	19
4	Structural and transport properties of highly Ru-deficient SrRu <sub>0.7</sub> O <sub>3</sub> thin films prepared by molecular beam epitaxy: Comparison with stoichiometric SrRuO <sub>3</sub> . AIP Advances, 2021, 11, .	0.6	18
5	Alternation of Magnetic Anisotropy Accompanied by Metal-Insulator Transition in Strained Ultrathin Manganite Heterostructures. Physical Review Applied, 2021, 15, .	1.5	4
6	Spin-orbit torque magnetization switching in a perpendicularly magnetized full Heusler alloy Co <sub>2</sub> FeSi. AIP Advances, 2021, 11, .	0.6	1
7	Unconventional bias dependence of tunnel magnetoresistance induced by the Coulomb blockade effect. AIP Advances, 2021, 11, 125029.	0.6	0
8	Room-temperature perpendicular magnetic anisotropy of Pt/Co/AlO <sub>x</sub> trilayers on SrTiO <sub>3</sub> (001). AIP Advances, 2020, 10, 105010.	0.6	0
9	Direct observation of the magnetic ordering process in the ferromagnetic semiconductor Ga <sub>1-x</sub> Mn <sub>x</sub> As via soft x-ray magnetic circular dichroism. Journal of Applied Physics, 2020, 128, .	1.1	8
10	Large tunnel magnetoresistance in a fully epitaxial double-barrier magnetic tunnel junction of Fe/MgO/Fe/Al <sub>2</sub> O <sub>3</sub> /Nb-doped SrTiO <sub>3</sub> . AIP Advances, 2020, 10, 085115.	0.6	5
11	Enhancement of the Spin Hall Angle by Interdiffusion of Atoms in $\text{Fe}/\text{Mn}/\text{Co}/\text{Mn}/\text{Fe}$ heterostructure. Physical Review Applied, 2020, 14, .		
12	Suppression of the field-like torque for efficient magnetization switching in a spin-orbit ferromagnet. Nature Electronics, 2020, 3, 751-756.	13.1	23
13	High-Mobility 2D Hole Gas at a SrTiO <sub>3</sub> Interface. Advanced Materials, 2020, 32, e1906003.	11.1	20
14	Temperature dependence of magnetic anisotropy in heavily Fe-doped ferromagnetic semiconductor (Ga,Fe)Sb. Journal of Applied Physics, 2020, 127, 023904.	1.1	6
15	Spin Hall Angle in an all-epitaxial single-crystal perovskite-oxide heterostructure of $\text{La}_{1-x}\text{Sr}_x\text{MnO}_3/\text{SrTiO}_3$ . Physical Review Applied, 2019, 11, .	1.3	23
16	Ultralow-Power Orbital-Controlled Magnetization Switching Using a Ferromagnetic Oxide Interface. Physical Review Applied, 2019, 12, .	1.5	3
17	Perpendicular magnetic resonance and control of magnetic anisotropy by epitaxial strain in the ferromagnetic semiconductor $\text{Ga}_{1-x}\text{Mn}_x\text{As}$ . Applied Physics Letters, 2019, 115, 092408.		

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19	Evidence for Spin-Triplet Electron Pairing in the Proximity-Induced Superconducting State of an Fe-Doped InAs Semiconductor. <i>Physical Review Letters</i> , 2019, 122, 107001.	2.9	11
20	Room-temperature side-gate-induced current modulation in a magnetic tunnel junction with an oxide-semiconductor barrier for vertical spin MOSFET operation. <i>Applied Physics Express</i> , 2019, 12, 023009.	1.1	7
21	Large terahertz magnetization response in ferromagnetic nanoparticles. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	8
22	In-plane to perpendicular magnetic anisotropy switching in heavily-Fe-doped ferromagnetic semiconductor (Ga,Fe)Sb with high Curie temperature. <i>Physical Review Materials</i> , 2019, 3, .	0.9	15
23	Quantum size effect in an Fe quantum well detected by resonant tunneling carriers injected from a $p$ -type Ge semiconductor electrode. <i>Applied Physics Letters</i> , 2018, 112, .	1.5	4
24	Large spin-valve effect in a lateral spin-valve device based on ferromagnetic semiconductor GaMnAs. <i>Applied Physics Express</i> , 2018, 11, 033003.	1.1	5
25	Proximity-Induced Superconductivity in a Ferromagnetic Semiconductor (In,Fe)As. <i>Journal of Physics: Conference Series</i> , 2018, 969, 012036.	0.3	4
26	Improved performance of a GaMnAs-based vertical spin electric double-layer transistor. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 090301.	0.8	3
27	Intrinsic transmission magnetic circular dichroism spectra of GaMnAs. <i>AIP Advances</i> , 2018, 8, 035009.	0.6	2
28	Large current modulation and tunneling magnetoresistance change by a side-gate electric field in a GaMnAs-based vertical spin metal-oxide-semiconductor field-effect transistor. <i>Scientific Reports</i> , 2018, 8, 7195.	1.6	8
29	Ultrafast magnetization modulation induced by the electric field component of a terahertz pulse in a ferromagnetic-semiconductor thin film. <i>Scientific Reports</i> , 2018, 8, 6901.	1.6	9
30	Artificial control of the bias-voltage dependence of tunnelling-anisotropic magnetoresistance using quantization in a single-crystal ferromagnet. <i>Nature Communications</i> , 2017, 8, 15387.	5.8	12
31	Origin of the large positive magnetoresistance of $\chi\text{MnAs}$ $G = e^2 \frac{M}{M_0} x$		
32	Observation of the inverse spin Hall effect in the topological crystalline insulator SnTe using spin pumping. <i>Physical Review B</i> , 2017, 96, .	1.1	10
33	Hidden peculiar magnetic anisotropy at the interface in a ferromagnetic perovskite-oxide heterostructure. <i>Scientific Reports</i> , 2017, 7, 8715.	1.6	6
34	Magnetic anisotropy control by applying an electric field to the side surface of ferromagnetic films. <i>Scientific Reports</i> , 2017, 7, 5618.	1.6	18
35	Reduction of the magnetic dead layer and observation of tunneling magnetoresistance in La <sub>0.67</sub> Sr <sub>0.33</sub> MnO <sub>3</sub> -based heterostructures with a LaMnO <sub>3</sub> layer. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	12
36	Fe concentration dependence of tunneling magnetoresistance in magnetic tunnel junctions using group-IV ferromagnetic semiconductor GeFe. <i>AIP Advances</i> , 2017, 7, 105202.	0.6	1

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37	Tunneling magnetoresistance in trilayer structures composed of group-IV-based ferromagnetic semiconductor $\text{Ge}_{1-x}\text{Fe}_x$ , $\text{MgO}$ , and $\text{Fe}$ . <i>Applied Physics Express</i> , 2016, 9, 123001.	1.1	3
38	Spin-dependent transport and current modulation in a current-in-plane spin-valve field-effect transistor. <i>Applied Physics Letters</i> , 2016, 109, 152403.	1.5	2
39	Sudden restoration of the band ordering associated with the ferromagnetic phase transition in a semiconductor. <i>Nature Communications</i> , 2016, 7, 12013.	5.8	15
40	Room-temperature local ferromagnetism and its nanoscale expansion in the ferromagnetic semiconductor $\text{Ge}_{1-x}\text{Fe}_x$ . <i>Scientific Reports</i> , 2016, 6, 23295.	1.6	20
41	Electronic structure near the Fermi level in the ferromagnetic semiconductor $\text{GaMnAs}$ studied by ultrafast time-resolved light-induced reflectivity measurements. <i>Physical Review B</i> , 2016, 93, .	1.1	10
42	Spin-dependent transport properties of a $\text{GaMnAs}$ -based vertical spin metal-oxide-semiconductor field-effect transistor structure. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	22
43	Intrinsic magneto-optical spectra of $\text{GaMnAs}$ . <i>Applied Physics Letters</i> , 2015, 106, .	1.5	7
44	Annealing-induced enhancement of ferromagnetism and nanoparticle formation in the ferromagnetic semiconductor $\text{GeFe}$ . <i>Physical Review B</i> , 2014, 90, .	1.1	17
45	Important role of the non-uniform $\text{Fe}$ distribution for the ferromagnetism in group-IV-based ferromagnetic semiconductor $\text{GeFe}$ . <i>Journal of Applied Physics</i> , 2014, 116, 173906.	1.1	9
46	Electronic Excitations of a Magnetic Impurity State in the Diluted Magnetic Semiconductor $(\text{Ga},\text{Mn})\text{As}$ . <i>Physical Review Letters</i> , 2014, 112, 107203.	2.9	22
47	Unveiling the impurity band induced ferromagnetism in the magnetic semiconductor $(\text{Ga},\text{Mn})\text{As}$ . <i>Physical Review B</i> , 2014, 89, .	1.1	76
48	Recent progress in III-V based ferromagnetic semiconductors: Band structure, Fermi level, and tunneling transport. <i>Applied Physics Reviews</i> , 2014, 1, 011102.	5.5	96
49	Anomalous Fermi level behavior in $\text{GaMnAs}$ at the onset of ferromagnetism. <i>Applied Physics Letters</i> , 2013, 103, 032411.	1.5	16
50	Spin-dependent tunneling transport in a ferromagnetic $\text{GaMnAs}$ and un-doped $\text{GaAs}$ double-quantum-well heterostructure. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	8
51	Spintronics materials and devices - ferromagnetic semiconductors and heterostructures. , 2012, , .		0
52	Magnetoresistance enhanced by inelastic cotunneling in a ferromagnetic $\text{MnAs}$ nanoparticle sandwiched by nonmagnetic electrodes. <i>Journal of Applied Physics</i> , 2012, 111, 063716.	1.1	2
53	Valence-band structure of ferromagnetic semiconductor $(\text{In},\text{Ga},\text{Mn})\text{As}$ . <i>Physical Review B</i> , 2012, 86, .	1.1	20
54	Nearly non-magnetic valence band of the ferromagnetic semiconductor $\text{GaMnAs}$ . <i>Nature Physics</i> , 2011, 7, 342-347.	6.5	128



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73	Tunneling magnetoresistance of MnAs thin film/GaAs <sup>∧</sup> •AlAs <sup>∧</sup> •GaAs:MnAs nanoclusters and its AlAs barrier thickness dependence. Applied Physics Letters, 2006, 89, 242106.	1.5	21
74	Tunneling magnetoresistance in GaMnAs <sup>∧</sup> •AlAs <sup>∧</sup> •InGaAs <sup>∧</sup> •AlAs <sup>∧</sup> •GaMnAs double-barrier magnetic tunnel junctions. Applied Physics Letters, 2005, 87, 012105.	1.5	32
75	Magneto-optical properties and Curie temperature of heavily Mn-doped quaternary alloy ferromagnetic semiconductor (InGaMn)As grown on InP. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 975-977.	1.3	0
76	Magnetic properties of heavily Mn-doped quaternary alloy ferromagnetic semiconductor (InGaMn)As grown on InP. Applied Physics Letters, 2003, 83, 2175-2177.	1.5	42
77	Growth and Properties of Quaternary Alloy Magnetic Semiconductor (InGaMn)As. Japanese Journal of Applied Physics, 2002, 41, L24-L27.	0.8	23